



PATENT
9862-000016/US

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

APPLICANTS: Yun-Jung LEE et al. CONF. NO.: 9195
SERIAL NO.: 10/632,825 GROUP: 2826
FILED: August 4, 2003 EXAMINER: Evan T. Pert
FOR: METHOD OF FORMING OXIDE LAYER USING ATOMIC
LAYER DEPOSITION METHOD AND METHOD OF FORMING
CAPACITOR OF SEMICONDUCTOR DEVICE USING THE
SAME

AMENDMENT AFTER FINAL

Customer Service Window
Randolph Building
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December 7, 2005

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EP 12/27/05*

Dear Sir:

Responsive to the Final Official Action dated October 17, 2005, the following amendments and remarks are respectfully submitted in connection with the above-referenced application.

Amendments to the claims begin on page 2 of this paper.

Remarks begin on page 13 of this paper.